

10/053,543

and forming said bit line on said second metal silicide] A method of manufacturing a semiconductor device, comprising the steps of:

forming first and second transistors on a main surface of a semiconductor substrate with a space between each other;

forming first metal silicide at a surface of a source/drain of said second transistor with a source/drain of said first transistor being covered by an insulating film;

forming an interlayer insulating film covering said first and second transistors;

forming in said interlayer insulating film a first contact hole reaching one of said source/drain of said first transistor;

forming a plug electrode in said first contact hole;

forming in said interlayer insulating film a second contact hole reaching one of said source/drain of said second transistor;

forming second metal silicide on said plug electrode; and

forming a bit line on said second metal silicide and an interconnection in said second contact hole.

*B¹
(cont'd)*
Please cancel claims 12 and 14.

REMARKS

Claim 13 is the only remaining claim. Claim 13 has been amended and claims 12 and 14 cancelled. Care has been exercised to avoid the introduction of new matter. Indeed, adequate descriptive support for the present Amendment should be apparent